

TECHNICAL REPORT

AMENDMENT 1

High-voltage direct current (HVDC) power transmission using voltage sourced converters (VSC)

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FOREWORD

This amendment has been prepared by subcommittee 22F: Power electronics for electrical transmission and distribution systems, of IEC technical committee 22: Power electronic systems and equipment.

The text of this amendment is based on the following documents:

DTR	Report on voting
22F/300A/DTR	22F/307/RVC

Full information on the voting for the approval of this amendment can be found in the report on voting indicated in the above table.

The committee has decided that the contents of this amendment and the base publication will remain unchanged until the stability date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

CONTENTS

Add the title of subclauses 5.3.4, subclause 5.3.5 and 5.6.12 as follows:

5.3.4 CTL topology with VSC cells in half-bridge topology

5.3.5 CTL topology with VSC cells in full-bridge topology

5.6.12 Dynamic braking system

Replace, in the list of figures, the titles of Figure 11 and Figure 12 as follows:

Figures 11 – Symbol of a turn-off semiconductor device and associated free-wheeling diode

Figure 12 – Symbol of an IGBT and associated free-wheeling diode

1 Scope

Replace, the last sentence of the first paragraph, by the following:

The scope includes 2-level and 3-level converters with pulse-width modulation (PWM), along with multi-level converters, modular multi-level converters and cascaded two-level converters, but excludes 2-level and 3-level converters operated without PWM, in squarewave output mode.

Figure 1– Major components that may be found in a VSC substation

Replace the footnote b by the following new footnote b:

In some designs of VSC, the VSC d.c. capacitor may be partly or entirely distributed amongst the three phase units of the VSC unit, where it is referred to as the d.c. cell or submodule capacitors.

3.3 Power semiconductor terms

Delete the first paragraph, that is the note and its contents.

3.3.1 switched valve devices

Replace the existing term 3.3.1 and its definition by the following new term, its definition and note:

3.3.1 turn-off semiconductor device

a controllable semiconductor device which may be turned on and off by a control signal, for example IGBT

NOTE There are several types of turn-off semiconductor devices which can be used in voltage sourced converters (VSC) for HVDC and currently the IGBT is the major device used in such converters. The term IGBT is used throughout this technical report to refer to the turn-off semiconductor device. However, the technical report is equally applicable to other types of devices with turn-off capability in most of the parts.

3.3.2 insulated gate bipolar transistor IGBT

Replace the definition of this term by the following new definition and note:

turn-off semiconductor device with three terminals: a gate terminal (G) and two load terminals emitter (E) and collector (C)

NOTE By applying the appropriate gate to the emitter voltages, current in one direction can be controlled, i.e. turned on and turned off.

3.3.3 free-wheeling diode FWD

Replace the definition of this term with the following new definition and notes:

power semiconductor device with diode characteristic

NOTE 1 A FWD has two terminals: an anode (A) and a cathode (K).

NOTE 2 The current through FWDs is in the opposite direction to the IGBT current.

NOTE 3 FWDs are characterized by the capability to cope with high rates of decrease of current caused by the switching behaviour of the IGBT.

3.4 VSC topologies

3.4.7

modular multi-level converter MMC

Replace the definition of this term with the following definition:

multi-level converter in which each VSC valve consists of a number of MMC building blocks connected in series

Add, after 3.4.23, the following new terms 3.4.24 and 3.4.25 and their definitions:

3.4.24

MMC building block

self-contained, two-terminal controllable voltage source together with d.c. capacitor(s) and immediate auxiliaries, forming part of a MMC

Add, after 3.4.24, the following new term 3.4.25 and its definition as shown below:

3.4.25

cascaded two-level (CTL) converter

modular multi-level converter in which each switch position consists of more than one IGBT-diode pair connected in series

3.4.10

VSC valve

Replace the definition of this term by the following two new subentries 3.4.10.1 and 3.4.10.2 and their definitions:

3.4.10.1

switch type VSC valve

arrangement of IGBT-diode pairs connected in series and arranged to be switched simultaneously as a single function unit

3.4.10.2

controllable voltage source type VSC valve

complete controllable voltage source assembly, which is generally connected between one a.c. terminal and one d.c. terminal

3.4.11

diode valve

Replace the existing definition of term 3.4.11 with the following new definition:

semiconductor valve containing diodes as the main semiconductor devices and associated circuits and components if any, which might be used in some VSC topologies

3.4.13

VSC valve level

Replace the existing definition and note of 3.4.13, by the following new definition and note:

the smallest indivisible functional unit of VSC valve

NOTE For any VSC valve in which IGBTs are connected in series and operated simultaneously, one VSC valve level is one IGBT-diode pair including its auxiliaries. For MMC type without IGBT-diode pairs connected in series one valve level is one submodule together with its auxiliaries.

3.4.15 redundant levels

Replace the existing definition of term 3.4.15 by the following definition and note:

maximum number of series connected VSC valve levels or diode valve levels in a valve that may be short-circuited externally or internally during service without affecting the safe operation of the valve as demonstrated by type tests, and which if, when exceeded, would require shutdown of the valve to replace the failed levels or acceptance of increased risk of failures

NOTE In valve designs such as the cascaded two-level converter, which contain two or more conduction paths within each cell and have series-connected VSC valve levels in each path, redundant levels shall be counted only in one conduction path in each cell.

3.4.17 submodule d.c. capacitor

Replace the term 3.4.17 and its definition by the following new term, definition and note:

3.4.17 d.c. capacitor

capacitor used as part of a voltage sourced converter which experiences mainly d.c. voltage between its terminals

NOTE For valves of the controllable switch type, the d.c. capacitor is usually arranged as a single device between the d.c. terminals. For valves of the controllable voltage-sourced type, the d.c. capacitor is usually distributed amongst the MMC building blocks.

3.4.18 valve reactor

Replace the existing definition of term 3.4.18 by the following new definition:

a reactor (if any) which is connected in series to a VSC valve of the controllable voltage-source type

NOTE One or more valve reactors can be associated to one VSC valve and might be connected at different positions within the valve. According to the definition, valve reactors are not part of the VSC valve. However, it is also possible to integrate the valve reactors in the structural design of the VSC valve, e.g. into each valve level.

3.4.19 valve structure

Replace the existing definition of term 3.4.19 by the following new definition:

structural components of a valve, required in order to physically support the valve modules

3.4.21 multiple valve unit MVU

Replace the existing definition of term 3.4.21 by the following new definition:

mechanical arrangement of 2 or more valves sharing a common valve support, where applicable

3.4.22 valve section

Replace the existing definition of term 3.4.22 by the following new definition and note:

electrical assembly, defined for test purposes, comprising a number of valve levels and other components, which exhibits pro-rated electrical properties of a complete valve

NOTE For valves of controllable voltage source type, the valve section shall include d.c. capacitor in addition to VSC valve levels.

3.4.23
valve base electronics
VBE

Replace existing definition of term 3.4.23 by the following new definition:

electronic unit, at earth potential, providing the electrical to optical conversion between the converter control system and the VSC valves

Add, after 3.4.25, the following new terms 3.4.26 and 3.4.27 and their definitions:

3.4.26
submodule

MMC building block where each switch position consists of only one IGBT-diode pair

3.4.27
cell

MMC building block where each switch position consists of more than one IGBT-diode pair connected in series

3.5.3
phase reactor

Replace existing definition of term 3.5.3 by the following new definition:

reactor connected directly to the a.c. terminal of the VSC phase unit, forming part of the coupling inductance

3.5.5
a.c. system side harmonic filter

Replace existing term 3.5.5 and its definition with the following new term, definition and note:

3.5.5
a.c. harmonic filters

filter circuits to prevent VSC-generated harmonics – if applicable – from penetrating into the a.c. system or to prevent amplification of background harmonics on the a.c. system

NOTE AC harmonic filters can be installed on either the line side or the converter side of the interface transformer.

3.5.7
HF blocking filter

Replace existing term 3.5.7 and its definition with the following term, definition and note:

3.5.7
high frequency filter
HF filter

filter circuits to prevent VSC-generated high frequency (HF) harmonics – if applicable – from penetrating into the a.c. system

NOTE High frequency filters can be installed on either the line side or the converter side of the interface transformer.

3.5.9
common mode blocking reactor

Replace the words “bipolar long distance” with the words “an HVDC” in the definition.

3.5.10**d.c. harmonic filter**

Replace the existing definition of term 3.5.10 by the following new definition and note:

d.c. filters (if any) used to prevent harmonics generated by VSC valve from penetrating into the d.c. system

NOTE The filter can consist of a tuned shunt branch, smoothing reactor or common mode blocking reactor or combinations thereof.

3.5.11**d.c. reactor**

Replace the existing definition of term 3.5.11 with the following new definition:

a reactor (if any) connected in series to a d.c. busbar

NOTE DC reactor is used to reduce harmonic currents flowing in the d.c. line or cable and to detune critical resonances within the d.c. circuit. A d.c. reactor might also be used for protection purposes.

3.6.3**STATCOM operation**

Replace the existing definition of term 3.6.3 with the following new definition:

mode of operation of a converter when only reactive power (capacitive or inductive) is exchanged with the a.c. system

3.6.13**blocked state**

Replace the existing definition of term 3.6.13 with the following definition:

condition in which all valves of the VSC unit are blocked

3.6.15**modulation index of PWM converters**

Replace the existing term 3.6.15 and its definition with the following new term and definition:

3.6.15**modulation index*****M***

ratio of the peak line to ground a.c. converter voltage, to half of the converter d.c. terminal to terminal voltage

$$M = \frac{\sqrt{2} \cdot U_{c1}}{\sqrt{3} \cdot \frac{U_{dc}}{2}}$$

where

U_{c1} is the r.m.s value of the fundamental frequency component of the line-to-line voltage U_c ,

U_c is the output voltage of one VSC phase unit at its a.c. terminal,

U_{dc} is the output voltage of one VSC phase unit at its d.c. terminals.

NOTE Some sources define modulation index in a different way such that a modulation index of 1 refers to a square-wave output, which means that the modulation index can never exceed 1. The modulation index according to that definition is given simply by $M (\pi/4)$. However, that definition is relevant mainly to two-level converters using PWM.

